

PATENT ABSTRACTS OF JAPAN

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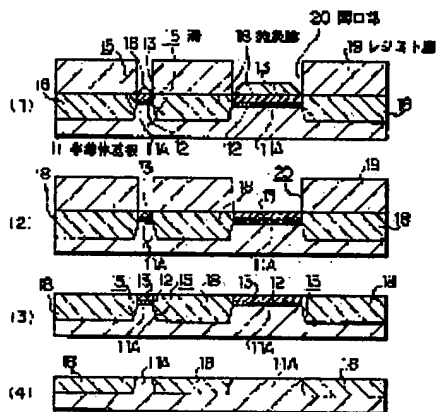
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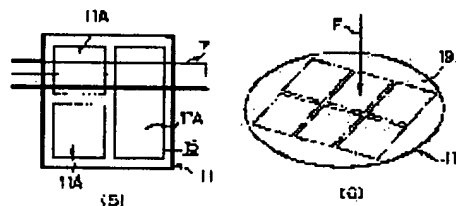
(54) MANUFACTURE OF SEMICONDUCTOR DEVICE



(57)Abstract:

PROBLEM TO BE SOLVED: To provide a technique by which an STI can be formed without performing CMP(chemical mechanical polishing) which raises a dishing problem nor requiring any active dummy pattern.

SOLUTION: A semiconductor device manufacturing method in which an element isolating area is formed by forming active area isolating grooves 15 into a semiconductor substrate 11 and filling up the grooves 15 with insulating films 18 includes a step of forming a resist film 19 on the insulating films 18 after forming the insulating films 18 on the semiconductor substrate 11 so that the films may fill up the grooves 15, a step of generating data about the positions of patterns in an active area isolated by the element isolating area by directly reading the positions, and a step of forming an opening 20 through the resist film 19 on the active area by exposing and developing the film 19, based on the data. The method also includes a step of selectively removing the insulating films 18 on the active area from the opening 20.



LEGAL STATUS

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